Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

HB857

APPLICATIONS

LOW FREQUENCY POWER AMPLIFIER

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature····· 150℃

P_C——Collector Dissipation (T_c=25℃) ····· 40W

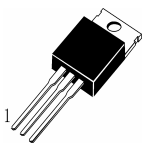
V_{CBO}——Collector-Base Voltage·····-70V

V_{CEO}——Collector-Emitter Voltage····· -50V

V_{EBO}——Emitter-Base Voltage····· -5V

I_C——Collector Current (DC) ····· -4A

TO-220



1—Base, B
2—Collector, C
3—Emitter, E

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-70			V	I_C=-10μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-50			V	I_C=-50mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-10μA, I_C=0
I_{CBO}	Collector Cut-off Current			-1	μA	V_{CB}=-50V, I_E=0
H_{FE} (1)	DC Current Gain	60		320		V_{CE}=-4V, I_C=-1A
H_{FE} (2)	DC Current Gain	35				V_{CE}=-4V, I_C=-0.1A
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-1	V	I_C=-2A, I_B=-0.2A
$V_{BE(on)}$	Base-Emitter On Voltage			-1	V	V_{CE}=-4V, I_C=-1A
ft	Current Gain-Bandwidth Product		15		MHz	V_{CE}=-4V, I_C=-0.5A,

h_{FE} Classification

B	C	D
60—120	100—200	160—320